

NTMD4820N

Power MOSFET

30 V, 8 A, Dual N-Channel, SOIC-8



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Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- Dual SOIC-8 Surface Mount Package Saves Board Space

Applications

- Disk Drives
- DC-DC Converters
- Printers

| $V_{(BR)DSS}$ | $R_{DS(on)}$ Max | I_D Max |
|---------------|------------------|-----------|
| 30 V | 20 mΩ @ 10 V | 8 A |
| | 27 mΩ @ 4.5 V | |

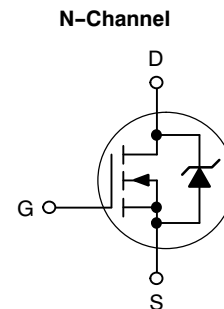
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

| Rating | Symbol | Value | Unit | |
|--|--|--------------------------|------------------|---|
| Drain-to-Source Voltage | V_{DSS} | 30 | V | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | |
| Continuous Drain Current $R_{\theta JA}$ (Note 1) | I_D | $T_A = 25^\circ\text{C}$ | 6.4 | A |
| | | $T_A = 70^\circ\text{C}$ | 5.1 | |
| Power Dissipation $R_{\theta JA}$ (Note 1) | P_D | 1.28 | W | |
| Continuous Drain Current $R_{\theta JA}$ (Note 2) | I_D | $T_A = 25^\circ\text{C}$ | 4.9 | A |
| | | $T_A = 70^\circ\text{C}$ | 3.9 | |
| Power Dissipation $R_{\theta JA}$ (Note 2) | P_D | 0.75 | W | |
| Continuous Drain Current $R_{\theta JA} t < 10$ s (Note 1) | I_D | $T_A = 25^\circ\text{C}$ | 8.0 | A |
| | | $T_A = 70^\circ\text{C}$ | 6.4 | |
| Power Dissipation $R_{\theta JA} t < 10$ s (Note 1) | P_D | 2.0 | W | |
| Pulsed Drain Current | I_{DM} | 32 | A | |
| | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | | | |
| Operating Junction and Storage Temperature | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ | |
| Source Current (Body Diode) | I_S | 1.7 | A | |
| Single Pulse Drain-to-Source Avalanche Energy $T_J = 25^\circ\text{C}, V_{DD} = 30$ V, $V_{GS} = 10$ V, $I_L = 11 A_{pk}, L = 1.0$ mH, $R_G = 25 \Omega$ | EAS | 60.5 | mJ | |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | |

THERMAL RESISTANCE RATINGS

| Rating | Symbol | Max | Unit |
|--|-----------------|-------|---------------------------|
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 97.5 | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient – $t \leq 10$ s (Note 1) | $R_{\theta JA}$ | 62 | |
| Junction-to-FOOT (Drain) | $R_{\theta JF}$ | 40 | |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 167.5 | |

1. Surface-mounted on FR4 board using 1 inch sq pad size, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.



MARKING DIAGRAM & PIN ASSIGNMENT



4820N = Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|------------------|------------------|
| NTMD4820NR2G | SOIC-8 (Pb-Free) | 2500/Tape & Reel |

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTMD4820N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)jk

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|----------------|--------|----------------|-----|-----|-----|------|
|----------------|--------|----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|---|--------------------------------------|--|------------------------|-----|------|-------|
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0 V, I _D = 250 μA | 30 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(BR)DSS} /T _J | | | 5.0 | | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V, V _{DS} = 24 V | T _J = 25°C | | 1.0 | μA |
| | | | T _J = 100°C | | 10 | |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = ±20 V | | | ±100 | nA |

ON CHARACTERISTICS (Note 3)

| | | | | | | |
|--|-------------------------------------|---|-----|----|-----|-------|
| Gate Threshold Voltage | V _{GS(TH)} | V _{GS} = V _{DS} , I _D = 250 μA | 1.5 | | 3.0 | V |
| Negative Threshold Temperature Coefficient | V _{GS(TH)} /T _J | | | 26 | | mV/°C |
| Drain-to-Source On Resistance | R _{DS(on)} | V _{GS} = 10 V, I _D = 7.5 A | | 15 | 20 | mΩ |
| | | V _{GS} = 4.5 V, I _D = 6.5 A | | 20 | 27 | |
| Forward Transconductance | g _{FS} | V _{DS} = 1.5 V, I _D = 7.5 A | | 21 | | S |

CHARGES, CAPACITANCES AND GATE RESISTANCE

| | | | | | | |
|------------------------------|---------------------|---|--|------|--|----|
| Input Capacitance | C _{ISS} | V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 15 V | | 940 | | pF |
| Output Capacitance | C _{OSS} | | | 225 | | |
| Reverse Transfer Capacitance | C _{RSS} | | | 125 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 7.5 A | | 7.7 | | nC |
| Threshold Gate Charge | Q _{G(TH)} | | | 1.1 | | |
| Gate-to-Source Charge | Q _{GS} | | | 3.3 | | |
| Gate-to-Drain Charge | Q _{GD} | | | 3.2 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 10 V, V _{DS} = 15 V, I _D = 7.5 A | | 15.2 | | nC |

SWITCHING CHARACTERISTICS (Note 4)

| | | | | | | |
|---------------------|---------------------|---|--|-----|--|----|
| Turn-On Delay Time | t _{d(ON)} | V _{GS} = 10 V, V _{DD} = 15 V, I _D = 1.0 A, R _G = 6.0 Ω | | 9.4 | | ns |
| Rise Time | t _r | | | 4.0 | | |
| Turn-Off Delay Time | t _{d(OFF)} | | | 21 | | |
| Fall Time | t _f | | | 6.5 | | |

DRAIN-TO-SOURCE CHARACTERISTICS

| | | | | | | | |
|-----------------------|-----------------|--|------------------------|------|------|-----|---|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V, I _D = 1.7 A | T _J = 25°C | | 0.75 | 1.0 | V |
| | | | T _J = 125°C | | 0.59 | | |
| Reverse Recovery Time | t _{RR} | V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 1.7 A | | 17.8 | | ns | |
| Charge Time | T _a | | | 8.3 | | | |
| Discharge Time | T _b | | | 9.5 | | | |
| Reverse Recovery Time | Q _{RR} | | | 8.0 | | nC | |

PACKAGE PARASITIC VALUES

| | | | | | | |
|-------------------|----------------|-----------------------|--|------|-----|----|
| Source Inductance | L _S | T _A = 25°C | | 0.66 | | nH |
| Drain Inductance | L _D | | | 0.20 | | nH |
| Gate Inductance | L _G | | | 1.50 | | nH |
| Gate Resistance | R _G | | | 1.5 | 3.0 | Ω |

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

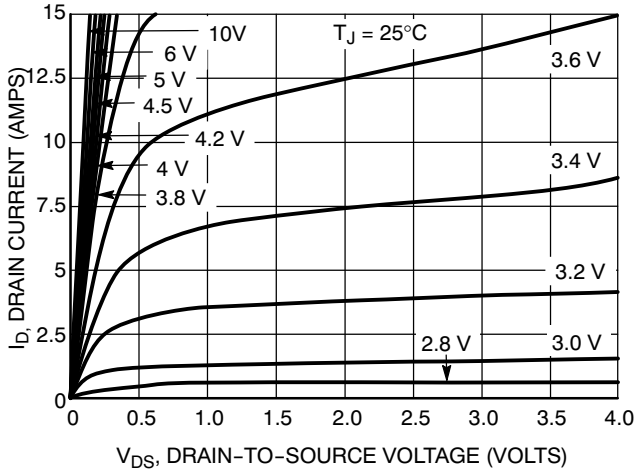


Figure 1. On-Region Characteristics

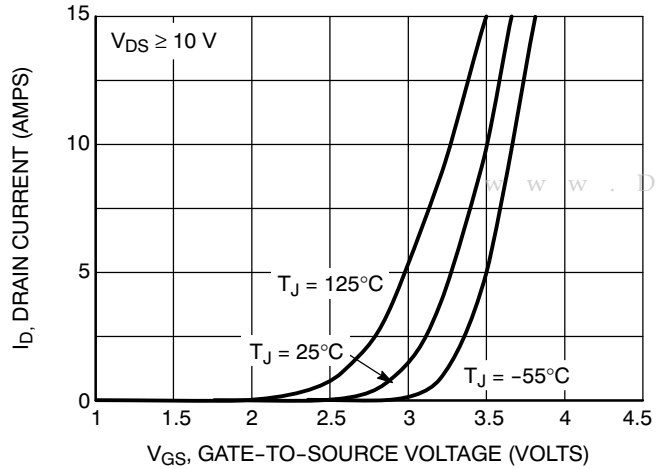


Figure 2. Transfer Characteristics

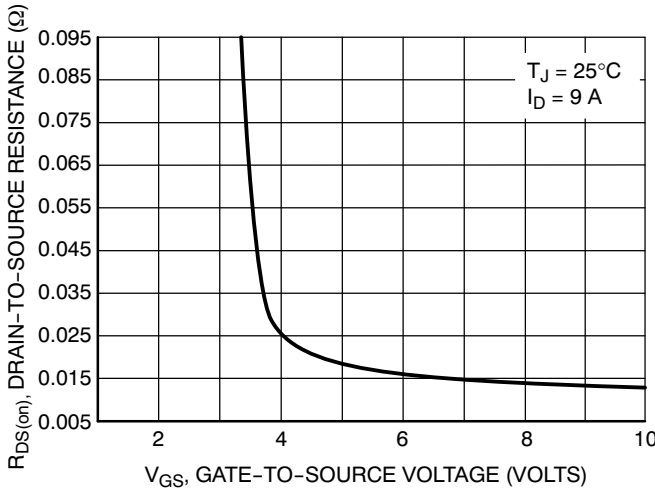


Figure 3. On-Resistance vs. Gate-to-Source Voltage

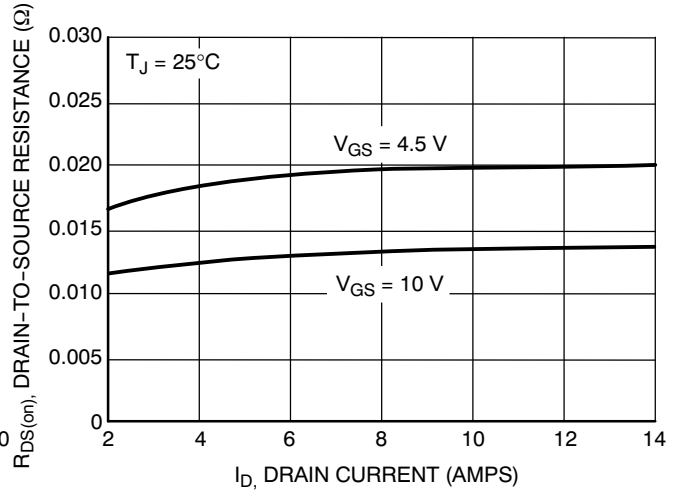


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

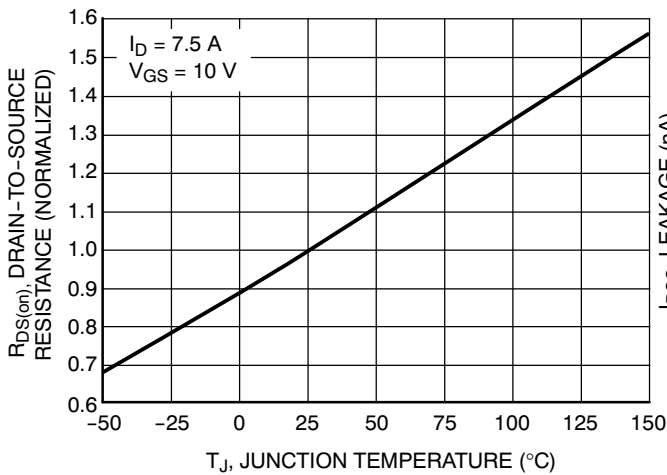


Figure 5. On-Resistance Variation with Temperature

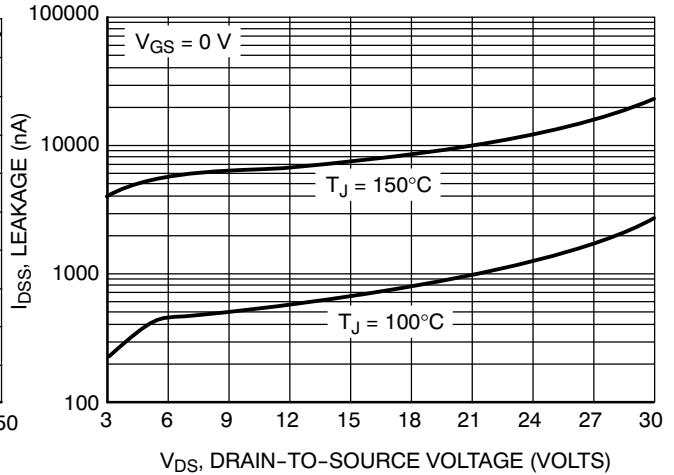


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL PERFORMANCE CURVES

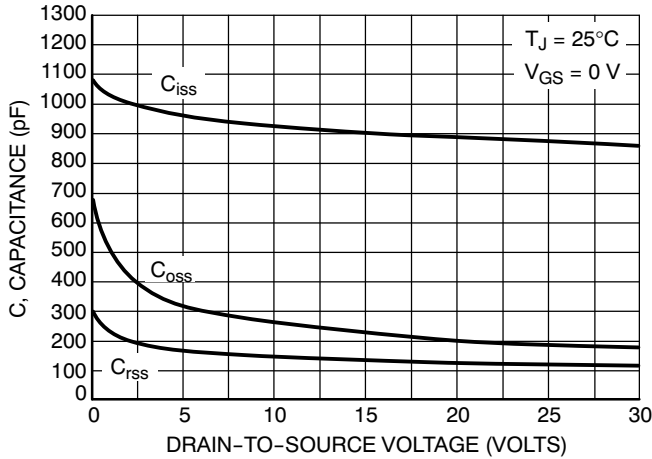


Figure 7. Capacitance Variation

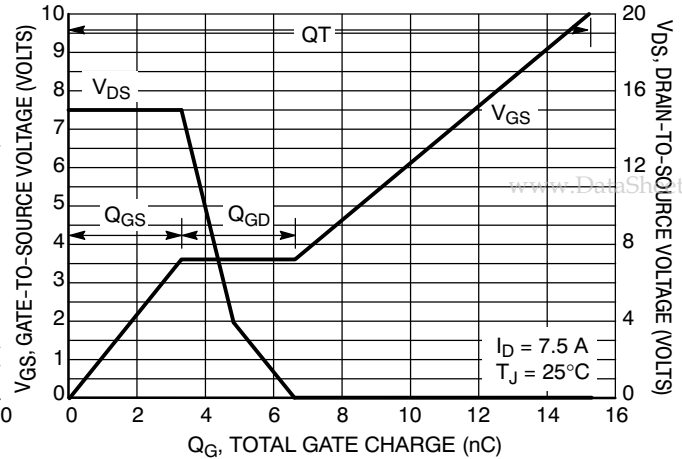


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

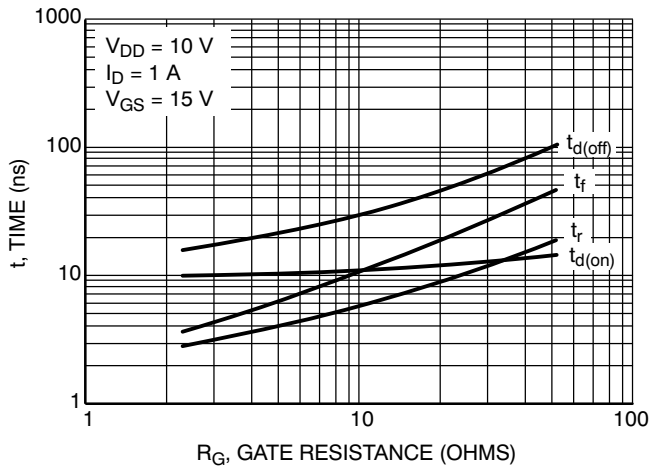


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

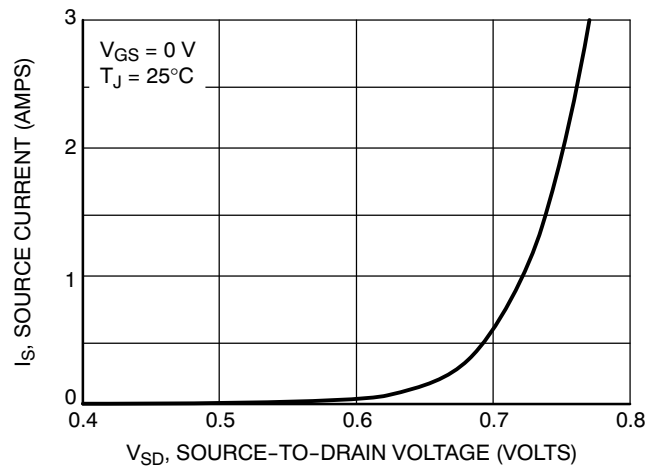


Figure 10. Diode Forward Voltage vs. Current

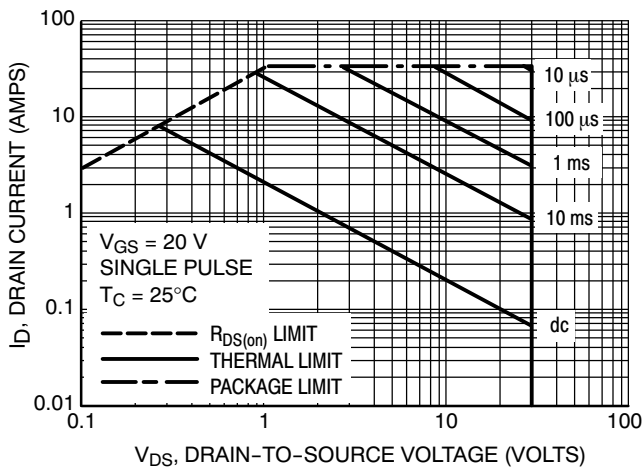


Figure 11. Maximum Rated Forward Biased Safe Operating Area

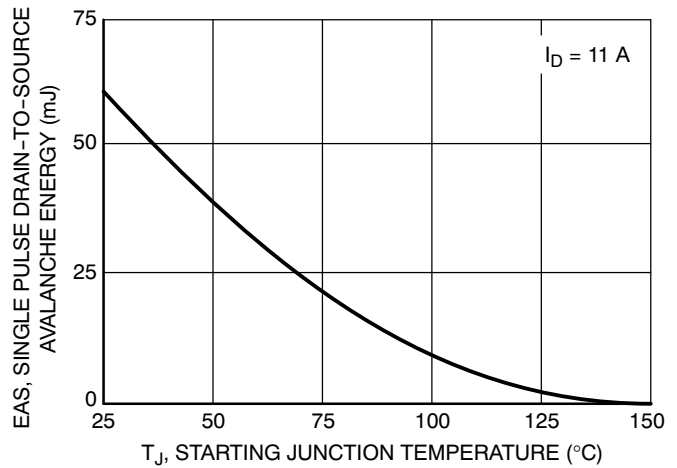
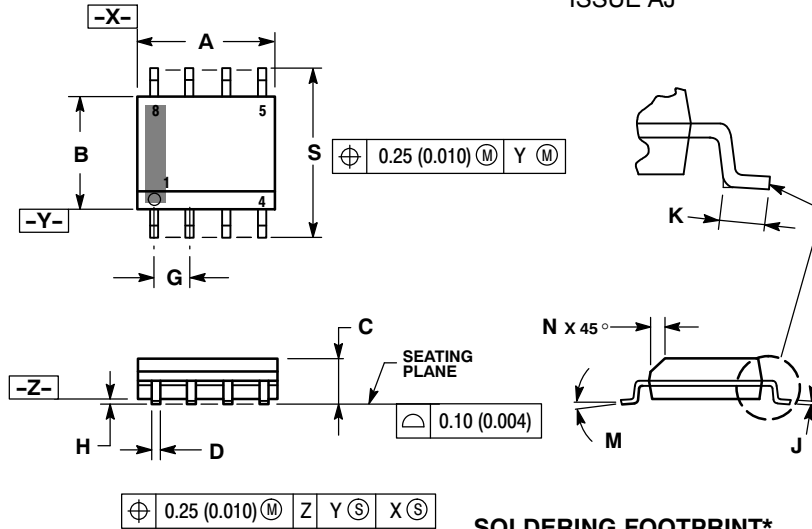


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 ISSUE AJ

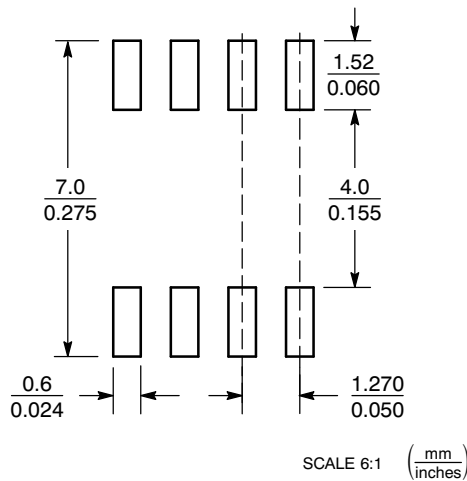


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0° | 8° | 0° | 8° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 11:

- PIN 1. SOURCE 1
- GATE 1
- SOURCE 2
- GATE 2
- DRAIN 2
- DRAIN 2
- DRAIN 1
- DRAIN 1

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